

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device comprising:
a translucent light-transmitting substrate;
a base film having a projection ~~a region of a first thickness and a region of a second thickness smaller than the first thickness~~, the film being formed over one surface of the translucent light-transmitting substrate, and ~~the region of the first thickness having an area smaller than the region of the second thickness~~; and
an island-like semiconductor layer having a crystal structure covering the projection and ~~extending over a pair of edges of the projection over the base film, the layer being formed over the region of the first thickness and the region of the second thickness.~~
2. (Currently Amended) A semiconductor device comprising a translucent light-transmitting substrate and a thin film transistor over the translucent light-transmitting substrate, wherein
a base film having a projection ~~a region of a first thickness and a region of a second thickness smaller than the first thickness~~ is provided over one surface of the translucent light-transmitting substrate;
~~the region of the first thickness has an area smaller than the region of the second thickness~~; and
an island like-semiconductor comprising a channel formation region, at least a part of [[a]] the channel formation region of the thin film transistor is provided over the projection, and region of the first thickness.

the island-like semiconductor layer covers the projection and extends over a pair of edges of the projection.

3. (Currently Amended) A semiconductor device according to claim 1, wherein a ~~difference in film thickness between the region of the first thickness and the region of the second thickness~~ a height of the projection is 30 to 100 nm.

4. (Currently Amended) A semiconductor device according to claim 2, wherein a ~~difference in film thickness between the region of the first thickness and the region of the second thickness~~ a height of the projection is 30 to 100 nm.

5. -10. (Canceled)

11. (New) A semiconductor device comprising:
a light-transmitting substrate;
a base film having a region of a first thickness and a region of a second thickness smaller than the first thickness, the film being formed over one surface of the light-transmitting substrate, and the region of the first thickness having an area smaller than the region of the second thickness; and

an island-like semiconductor layer having a crystal structure over the base film, the layer being formed over the region of the first thickness and the region of the second thickness,

wherein the island-like semiconductor layer is capable of being irradiated with light from another surface of the light-transmitting substrate through the region of the first thickness and the region of the second thickness.

12. (New) A semiconductor device comprising a light-transmitting substrate and a thin film transistor over the light-transmitting substrate, wherein

a base film having a region of a first thickness and a region of a second thickness smaller than the first thickness is provided over one surface of the light-transmitting substrate;

the region of the first thickness has an area smaller than the region of the second thickness;

at least a part of a channel formation region of the thin film transistor is provided over the region of the first thickness;

source and drain regions of the thin film transistor are provided over the projection and cover a pair of edges of the projection, and

the island-like semiconductor layer is capable of being irradiated with light from another surface of the light-transmitting substrate through the region of the first thickness and the region of the second thickness.

13. (New) A semiconductor device according to claim 11, wherein a difference in film thickness between the region of the first thickness and the region of the second thickness is 30 to 100 nm.

14. (New) A semiconductor device according to claim 12, wherein a difference in film thickness between the region of the first thickness and the region of the second thickness is 30 to 100 nm.